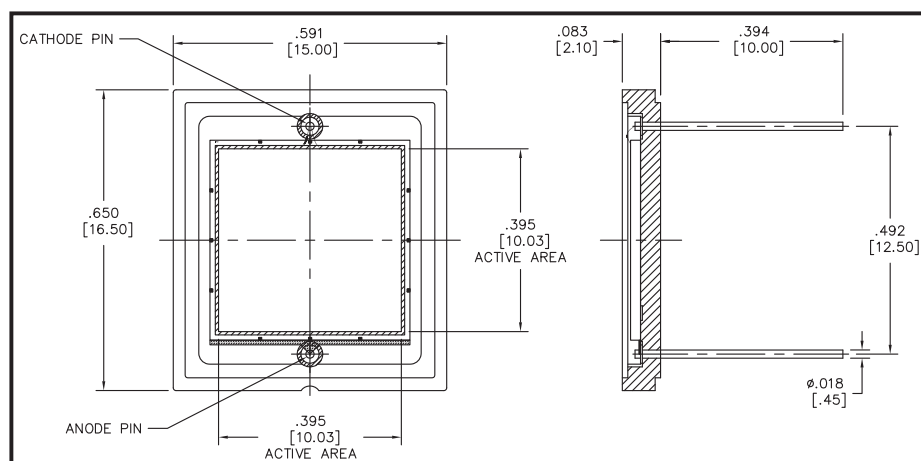


**FEATURES**

- Ideal for electron detection
- Large detection area
- 100% internal QE

Dimensions are in inch [metric] units.

ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area	10mm x 10mm		100		mm ²
Responsivity, $\mathcal{R}$	(see graphs on next page)				A/W
Shunt Resistance, R_{sh}	$V_B = \pm 10\text{mV}$	10	50		M-ohm
Reverse Breakdown Voltage, V_R	$I_R = 1\mu\text{A}$	5	10		Volts
Capacitance, C	$V_R = 0\text{V}$		10	44	nF
Rise Time	$V_R = 0\text{V}, R_L = 50\Omega$		10		usec

THERMAL PARAMETERS

Storage and Operating Temperature Range	-40°C TO 70°C
Maximum Junction Temperature	70°C
Lead Soldering Temperature ¹	260°C

¹0.08" from case for 10 seconds.

Shipped with temporary cover to protect photodiode and wire bond. Review Opto Diode "Handling Precautions for IRD Detectors" prior to removing cover.

